

AMENDMENTS TO THE CLAIMS

Claims 1-10. (Canceled).

11. (Currently Amended) A structure for creating chalcogenide integrated circuit devices, comprising:

a first layer comprising a conductive material;

a chalcogenide layer overlying the first layer;

a silver layer overlying the chalcogenide layer; and

a barrier layer on the silver layer, the barrier layer being essentially transparent to radiation.

12. (Previously Presented) A structure for creating chalcogenide integrated circuit devices, comprising:

a first layer;

a chalcogenide layer overlying the first layer;

a metal layer overlying the chalcogenide layer; and

chalcogenide barrier layer on the metal layer, the barrier layer being essentially transparent to radiation.

13. (Previously Presented) The structure of claim 12, wherein the chalcogenide barrier and the chalcogenide layer are formed of the same material.

14. (Original) The structure of claim 12, wherein the same material is GeSe.

15. (Original) The structure of claim 13, wherein the metal layer includes silver.

Claims 16-107. (Cancelled).

108. (Original) The structure of claim 11 wherein the barrier layer is transparent to light.

109. (Previously Presented) The structure of claim 12 wherein the barrier layer comprises germanium-selenide.

110. (Previously Presented) The structure of claim 11 wherein the barrier layer reduces agglomeration from the silver layer.

111. (Previously Presented) The structure of claim 11 wherein the silver layer is formed to a thickness in a range of about 100Å to about 200Å.

112. (Original) The structure of claim 11 wherein the barrier layer is formed to a thickness in a range of about 20Å to about 50Å.

113. (Original) The structure of claim 11 wherein the barrier layer is formed to a thickness of about 30Å.

114. (Original) The structure of claim 11 wherein the chalcogenide layer is formed to a thickness in a range of about 500Å to about 1000Å.

Claims 115-145. (Cancelled).